MMBT4403 (PNP)

FEATURES

Switching transistor)

Marking:2T

1. BASE
2. EMITTER
3. COLLECTO

SOT-23

MAXIMUM RATINGS (TA=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-40	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current -Continuous	I_C	600	mA
Collector Power Dissipation	P_C	300	mW
Junction Temperature	T_J	150	℃
Storage Temperature	Tstg	-55 to +150	℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	VCBO	IC=-100μA , IE=0	-40		V
Collector-emitter breakdown voltage	VCEO	IC= -1mA , IB=0	-40		V
Emitter-base breakdown voltage	VEBO	IE=-100μA, IC=0	-5		V
Collector cut-off current	ICBO	VCB=-35V, IE=0		-0.1	μA
Collector cut-off current	ICEO	VCE=-35 V, IB=0		-0.1	μA
Emitter cut-off current	IEBO	VEB=-4V,IC=0		-0.1	μA
DC current gain	hFE	VCE=-2V, IC= -150mA	100	300	
Collector-emitter saturation voltage	VCE(sat)	IC=-150mA, IB=-15mA		-0.4	V
Base-emitter saturation voltage	VBE(sat)	IC=- 150mA, IB=-15mA		-0.95	V
Transition frequency	f T	VCE= -10V, IC= -20mA f = 100MHz	200		MHz

MMBT4403 Typical Characteristics

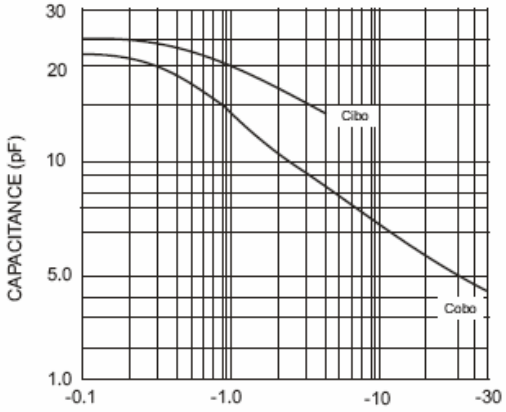

Fig. 1 Typical Capacitance

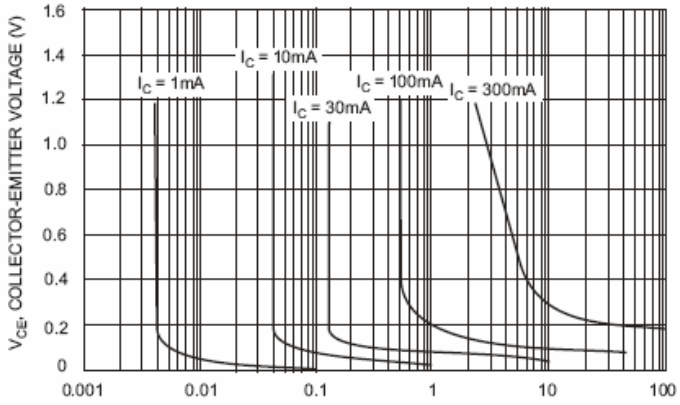

Fig. 2 Typical Collector Saturation Region

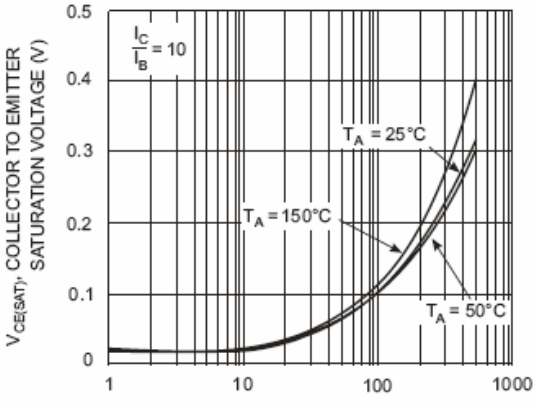

Fig. 3 Collector Emitter Saturation Voltage vs. Collector Current

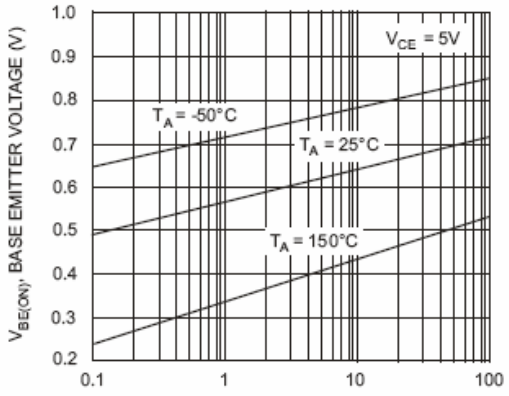

Fig. 4 Base-Emitter Voltage vs. Collector Current